

Measurements and irradiation at CERN

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INFN-FBK Meeting

23.8.2010

Outline

- **Lab-test measurements of proton irradiated assemblies**
 - 2E-, 3E-, 4E-type (1st batch)
 - Irradiated with 25MeV proton in Karlsruhe (by Bonn) up to $5.4 \text{ E}14 \text{ p/cm}^2$ (**1 E15 n_{eq}**)
 - Leakage current at different temperatures
 - Noise vs bias voltage at different temperatures
 - γ -source test measurement (self-trigger) at different bias voltages
 - β -source test measurement (triggered externally by scintillator) at different bias voltages

Preliminary results (by CERN group) are available at:

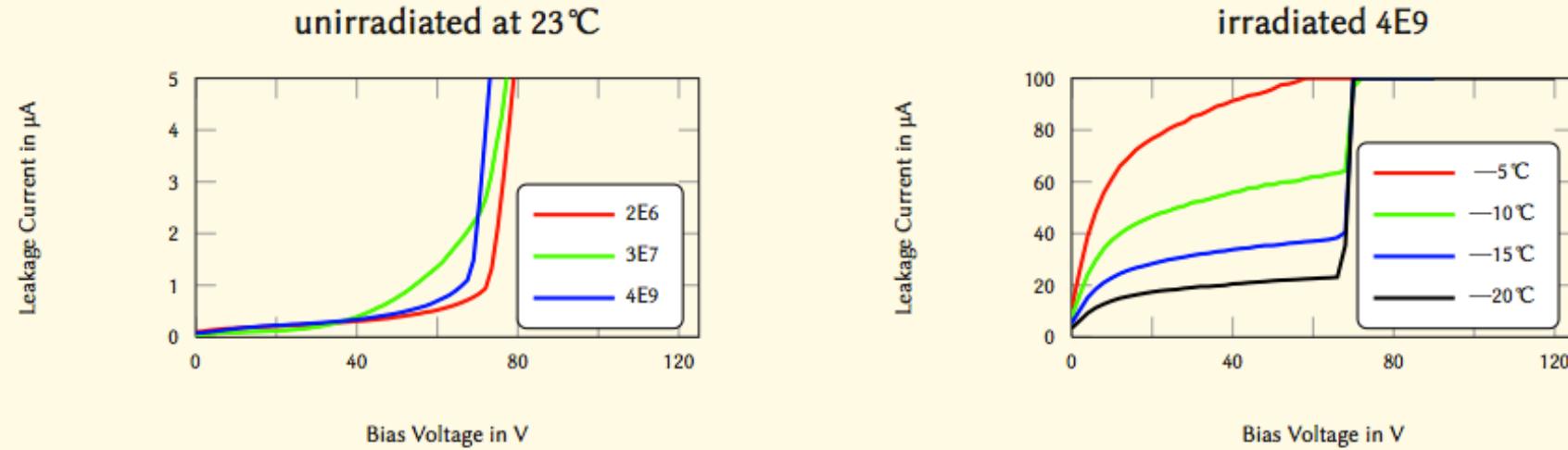
<https://twiki.cern.ch/twiki/pub/Main/CernAtlasPixelSensorsRD/3D-100629.pdf>

https://twiki.cern.ch/twiki/pub/Main/CernAtlasPixelSensorsRD/FBK_irradiated_Measurements_CERN.pdf

Results in agreement with Bonn:

<http://indico.cern.ch/getFile.py/access?contribId=15&resId=0&materialId=slides&confId=97122> (pwd: 3Ddream)
- SCAs sent back to Bonn for second irradiation step (**2 E15 n_{eq}**)
- Looking forward to test neutron irradiated assemblies
- PS Irradiation of 3D/FBK diodes concluded - devices ready for the shipment
- Have in planning to irradiate 2E and 4E with 24GeV proton beam (CERN PS) in October
- Announcement:
 - ATLAS 3D Rad Hard WG on Sept. 14th at 5pm CEST
 - Next ATLAS 3D testbeam: Oct. 11-21

Leakage current overview



Damage rate α

$$\frac{I_{\text{Vol}}}{V_{\text{ol}}} = \frac{I_{\text{Vol}, \Phi=0}}{V_{\text{ol}}} + \alpha \Phi$$

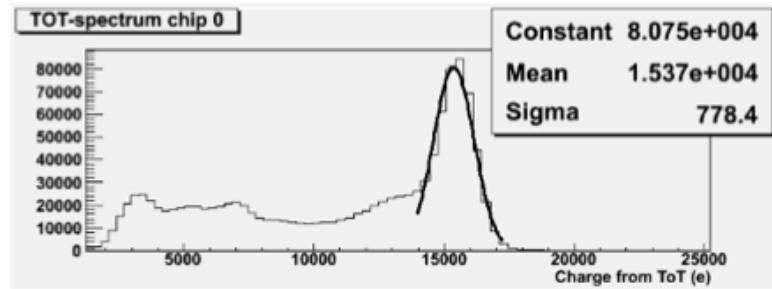
Sensor	2E6	3E7	4E9
α in $10^{-17} \frac{\text{A}}{\text{cm}}$	5.40	5.39	5.28

In agreement with published results!

M. Moll - Radiation Damage in Silicon Particle Detectors

Source-tests overview (241Am)

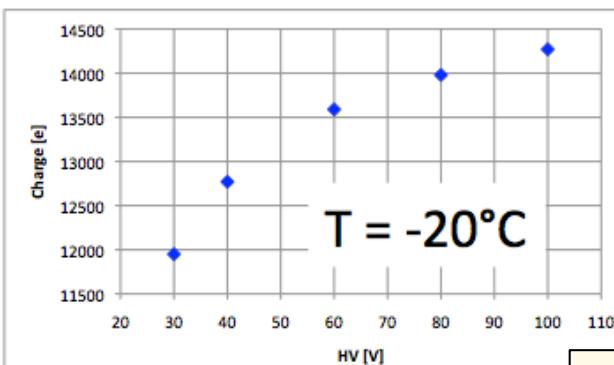
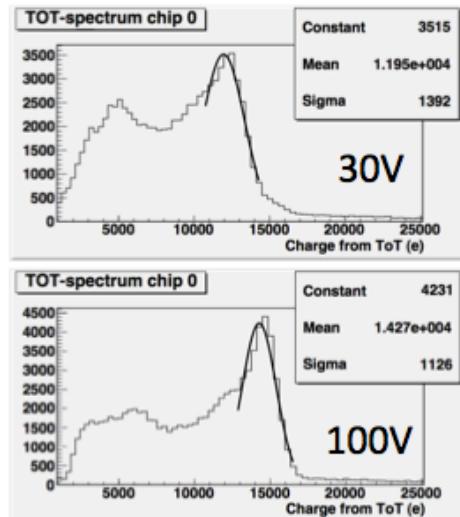
- Before irradiation ($T=22^\circ\text{C}$ and $\text{HV}=35\text{V}$)



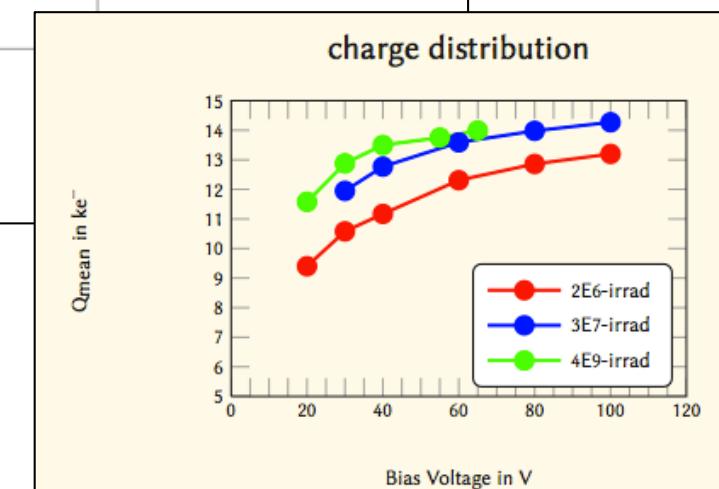
3E-TYPE

Shows the source spectrum as a sum over all pixels without any clustering.

- Measurements at different bias after irradiation ($1 \text{ E}15 \text{n}_{\text{eq}}$)



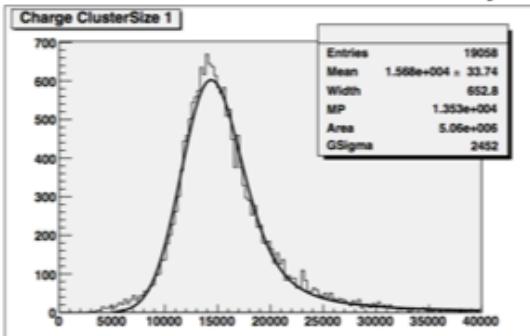
ATLAS 3D - Testbeam Meeting, 30.6.2010 - Alessandro La Rosa (CERN)



INFN-FBK Meeting, 23.8.2010 - Alessandro La Rosa (CERN)

Source-tests overview (Sr90)

- Before irradiation ($T=22^\circ\text{C}$ and $\text{HV}=35\text{V}$)

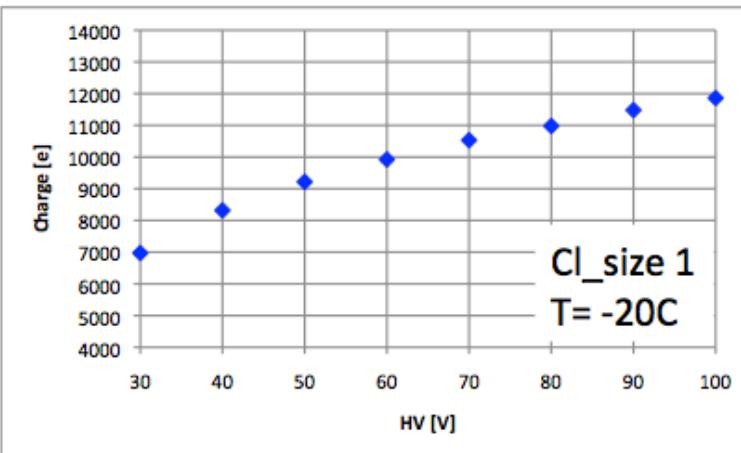


3E-TYPE

Cl_size 1: MPV = 13.53 ke-

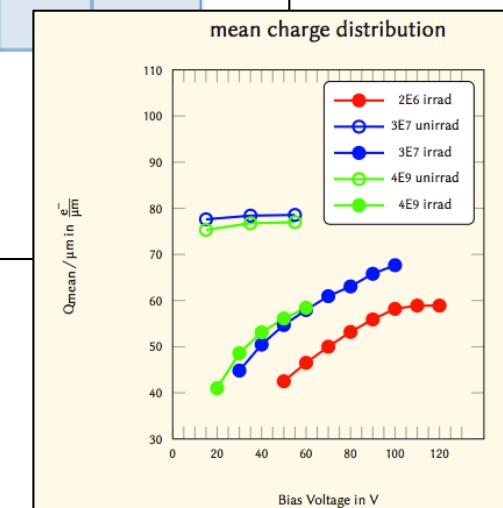
Expected value if we compare it with what has been obtained from Planar pixel sensor (250um thick):
16.02 ke- (Cl_size 1)

- Measurements at different bias after irradiation ($1 \text{ E}15 \text{n}_{\text{eq}}$)



HV	30V	40V	60V	80V	100V
Lost charge	49%	40%	30%	21%	15%

ATLAS 3D - Processing Meeting. 7.7.2010 - Alessandro La Rosa (CERN)



INFN-FBK Meeting. 23.8.2010 - Alessandro La Rosa (CERN)